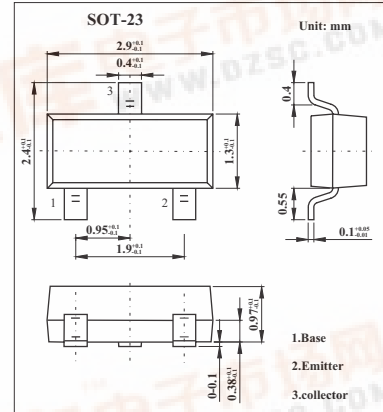


SMD Type Transistors

Silicon NPN Epitaxial
2SC2732

■ Features

- UHF frequency converter



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	I _C	20	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	4			V
Collector cutoff current	I _{CBO}	V _{CB} = 10V, I _C = 0			0.5	μA
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 10 mA, I _B = 1 mA			5	V
DC current transfer ratio	h _{FE}	V _{CE} = 10 V, I _C = 3 mA	30	60		
Gain bandwidth product	f _T	V _{CE} = 10 V, I _C = 5 mA	700	1000		MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		0.5	0.8	pF
Conversion gain	CG	V _{CC} = 12 V, I _C = 1 mA, f = 900 MHz, f _{osc} = 930 MHz (0dBm), f = 30 MHz		7.0		dB
Noise figure	NF	V _{CC} = 12 V, I _C = 1 mA, f = 900 MHz, f _{osc} = 930 MHz (0dBm), f _{out} = 30 MHz		10.0		dB

■ Marking

Marking	EC
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